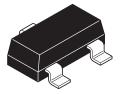
30V P-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

 $V_{(BR)DSS} = -30V$; $R_{DS(ON)} = 0.21\Omega$; $I_D = -1.6A$

DESCRIPTION

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



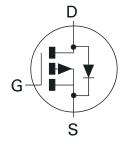
SOT23

FEATURES

- Low on-resistance
- · Fast switching speed
- · Low threshold
- Low gate drive
- SOT23 package

APPLICATIONS

- DC DC converters
- Power management functions
- Disconnect switches
- Motor control



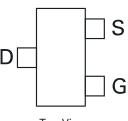
ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL	
ZXMP3A13FTA	7″	8mm	3000 units	
ZXMP3A13FTC	13"	8mm	10000 units	

DEVICE MARKING

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Top View



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DSS}	-30	V
Gate Source Voltage	V _{GS}	±20	V
Continuous Drain Current $V_{GS}=10V; T_A=25^{\circ}C$ (b) $V_{GS}=10V; T_A=70^{\circ}C$ (b) $V_{GS}=10V; T_A=25^{\circ}C$ (a)	I _D	-1.6 -1.3 -1.4	А
Pulsed Drain Current (c)	I _{DM}	-6	А
Continuous Source Current (Body Diode) (b)	Is	-1.2	А
Pulsed Source Current (Body Diode) (c)	I _{SM}	-6	А
Power Dissipation at T _A =25°C (a) Linear Derating Factor	P _D	625 5	mW mW/°C
Power Dissipation at T _A =25°C (b) Linear Derating Factor	P _D	806 6.4	mW mW/°C
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150	°C

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to ambient (a)	$R_{\theta JA}$	200	°C/W
Junction to ambient (b)	$R_{\theta JA}$	155	°C/W

NOTES

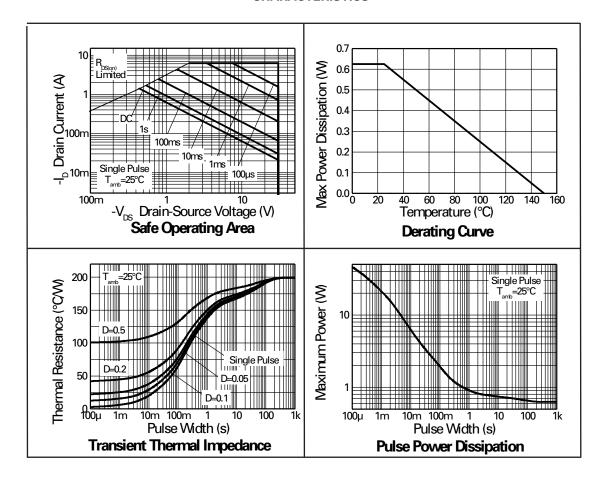


 $⁽a) For a device surface mounted on 25 mm\ x\ 25 mm\ FR4\ PCB\ with\ high\ coverage\ of\ single\ sided\ 1oz\ copper,\ in\ still\ air\ conditions$

⁽b) For a device surface mounted on FR4 PCB measured at t≤5 secs.

⁽c) Repetitive rating 25mm \times 25mm FR4 PCB, D = 0.05, pulse width $10\mu s$ - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

CHARACTERISTICS





ELECTRICAL CHARACTERISTICS (at $T_A = 25$ °C unless otherwise stated)

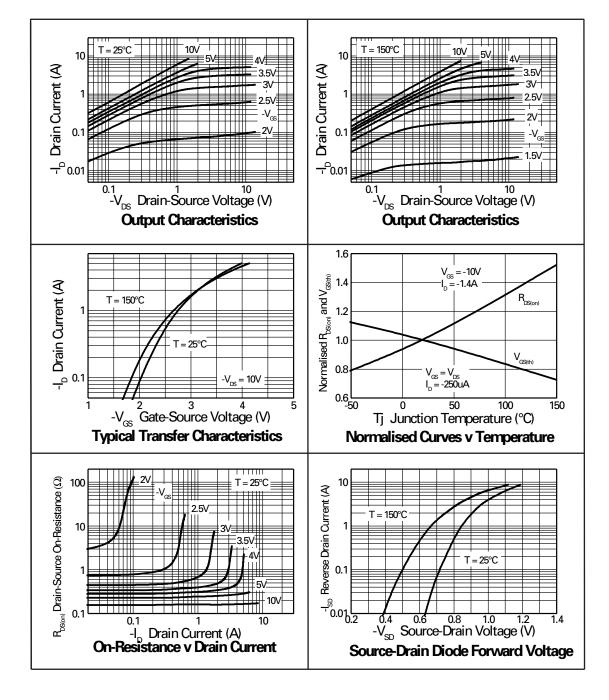
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS		
STATIC								
Drain-Source Breakdown Voltage	V _{(BR)DSS}	-30			V	I _D =-250μA, V _{GS} =0V		
Zero Gate Voltage Drain Current	I _{DSS}			-0.5	μΑ	V _{DS} =-30V, V _{GS} =0V		
Gate-Body Leakage	I _{GSS}			100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$		
Gate-Source Threshold Voltage	V _{GS(th)}	-1.0			V	I _D =-250μA, V _{DS} = V _{GS}		
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.210 0.330	Ω	V _{GS} =-10V, I _D =-1.4A V _{GS} =-4.5V, I _D =-1.1A		
Forward Transconductance (1)(3)	g _{fs}		2.4		S	V _{DS} =-15V,I _D =-1.4A		
DYNAMIC (3)			•			•		
Input Capacitance	C _{iss}		206		pF			
Output Capacitance	Coss		59.3		pF	V _{DS} =-15V, V _{GS} =0V, f=1MHz		
Reverse Transfer Capacitance	C _{rss}		49.2		pF	1-111112		
SWITCHING(2) (3)			•					
Turn-On Delay Time	t _{d(on)}		1.5		ns			
Rise Time	t _r		3.0		ns	V _{DD} =-15V, I _D =-1A		
Turn-Off Delay Time	t _{d(off)}		11.1		ns	$R_{G}=6.0\Omega$, $V_{GS}=-10V$		
Fall Time	t _f		7.6		ns			
Gate Charge	Qg		3.8		nC	V _{DS} =-15V,V _{GS} =-5V, I _D =-1.4A		
Total Gate Charge	Q_g		6.4		nC			
Gate-Source Charge	Q _{gs}		0.69		nC	V _{DS} =-15V,V _{GS} =-10V, I _D =-1.4A		
Gate-Drain Charge	Q_{gd}		2.0		nC			
SOURCE-DRAIN DIODE		•				•		
Diode Forward Voltage (1)	V _{SD}		-0.85	-0.95	V	T _J =25°C, I _S =-1.1A, V _{GS} =0V		
Reverse Recovery Time (3)	t _{rr}		15.6		ns	T _J =25°C, I _F =-0.95A,		
Reverse Recovery Charge (3)	O _{rr}		9.6		nC	di/dt= 100A/μs		

NOTES:

- (1) Measured under pulsed conditions. Width=300 $\mu s.$ Duty cycle $\leq~2\%$.
- (2) Switching characteristics are independent of operating junction temperature.
- (3) For design aid only, not subject to production testing.

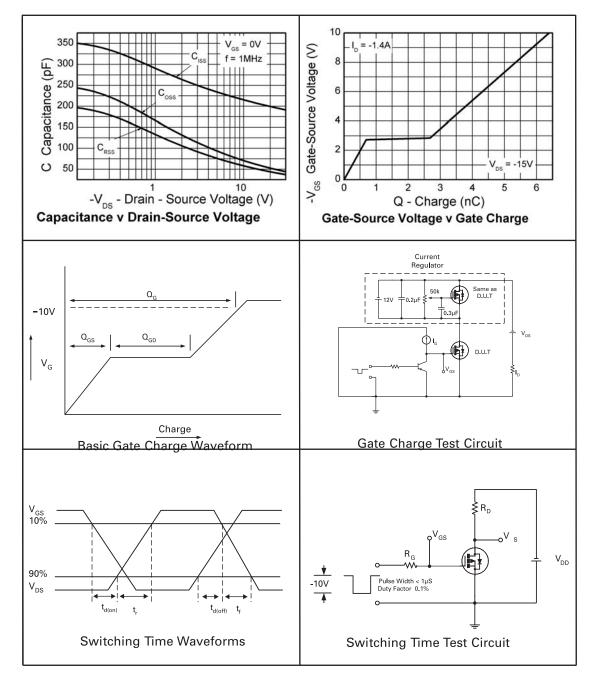


TYPICAL CHARACTERISTICS





TYPICAL CHARACTERISTICS





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Product status key:

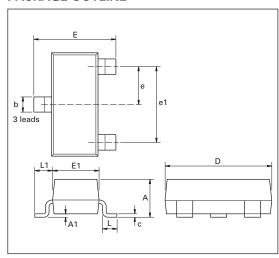
- "Preview"Future device intended for production at some point. Samples may be available
- "Active"Product status recommended for new designs
- "Last time buy (LTB)"Device will be discontinued and last time buy period and delivery is in effect
- "Not recommended for new designs"Device is still in production to support existing designs and production
- "Obsolete"Production has been discontinued

Datasheet status key:

- "Draft version"This term denotes a very early datasheet version and contains highly provisional
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- "Issue"This term denotes an issued datasheet containing finalized specifications. However, changes to specifications may occur, at any time and without notice.



PACKAGE OUTLINE



PACKAGE DIMENSIONS

DIM	Millimeters		Inches			Millimeters		Inches	
	Min	Max	Min	Max	DIM	Min	Max	Min	Max
Α	-	1.12	-	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	Е	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
С	0.085	0.020	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
е	0.95 NOM 0.037 NOM		NOM	_	_	_	_	_	

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